

ATR-FTIR Experiments with Chlorosilanes

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Abstract. OH groups on the surface of semiconductors (SC) such as Si, Ge, TiO₂, SnO₂ react with Cl–Si groups to give stable SC–O–Si bonds. ATR-FTIR is applied to study the infrared spectra of adsorbed H₈Si₈O₁₂ on ZnSe and Cl₈Si₈O₁₂ which has reacted with the surface –OH group of Ge. A comparison is made with the spectra of the free molecules.

Key words: cage molecules, silsesquioxanes, surface modification, infrared spectroscopy, ATR spectroscopy.

One highly successful form of surface modification is silanization. A silane containing a hydrolytically unstable bond will react with a surface OH group to form a silyl ether bond to the substrate [1]: $-\text{OH} + \text{X}-\text{Si}- \rightarrow -\text{O}-\text{Si}- + \text{HX}$. FTIR spectroscopy has proved to be very useful in providing information on such surface layers [2]. If the substrate is a sufficiently transparent crystal, very interesting studies can be made by means of the attenuated total internal reflection (ATR) spectroscopy [3]. ATR-FTIR spectroscopy can be applied to follow adsorption kinetics or reaction kinetics of surface modification [4] and to study photochemical, photoelectrochemical and electrochemical reactions on semiconductor surfaces.

We report first experiments with R₈Si₈O₁₂ (R = H, Cl) molecules. The synthesis of these molecules has been described in ref. [5]. Its structure is shown in Fig. 1 and the infrared spectrum of H₈Si₈O₁₂ is drawn in Fig. 2. Due to the O_h symmetry of this molecule, only the 6 $T_{1u} \leftarrow A_{1g}$ transitions are infrared active. We name them $\nu_1, \nu_2, \nu_3, \nu_4, \nu_5, \nu_6$, where ν_1 corresponds to the Si–H stretching mode, ν_3 to the Si–H bending mode and ν_2 is the Si–O stretching vibration. The assignment of the other frequencies is not yet definitive. From 4000 to 700 cm⁻¹, the spectrum was measured in CCl₄, and from 700 to 40 cm⁻¹ in a polyethylene wafer at room temperature.

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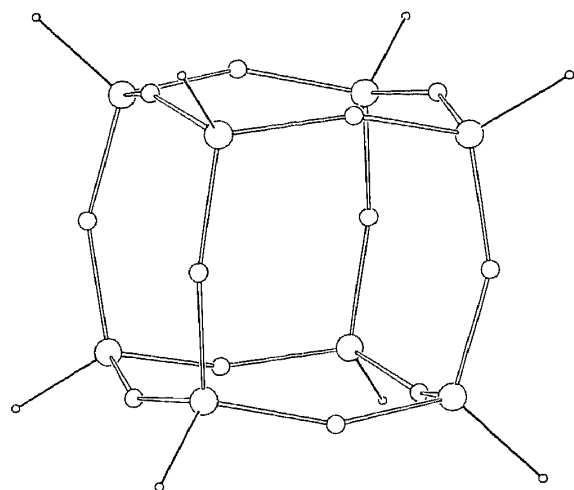


Fig. 1. Structure of $R_8Si_8O_{12}$

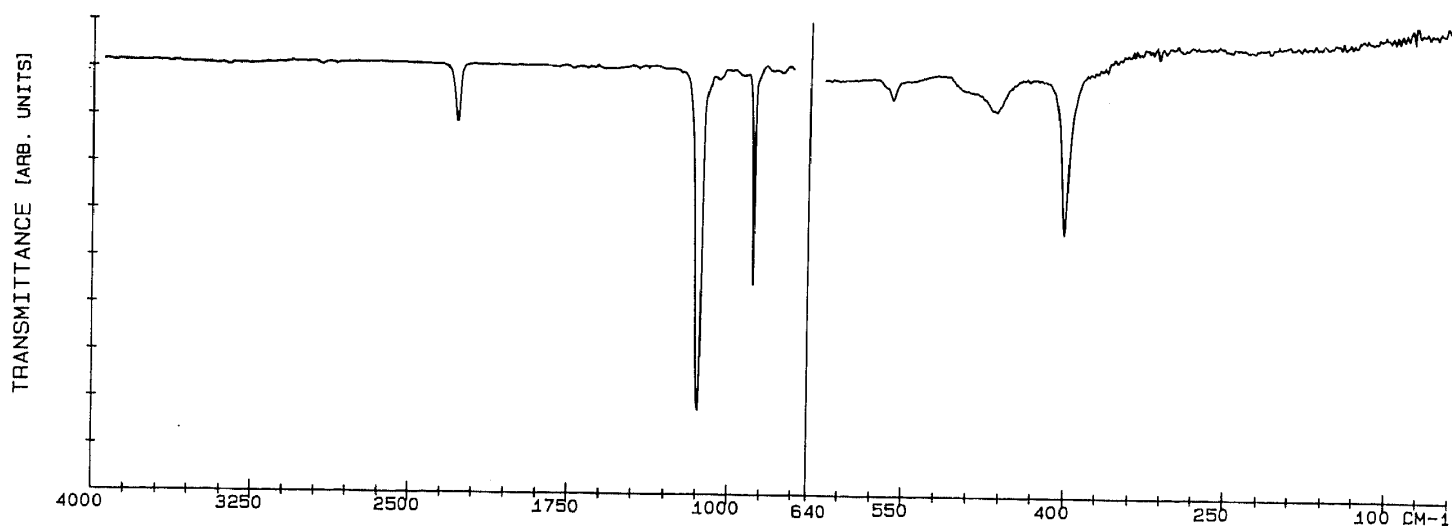


Fig. 2. Infrared spectrum of $H_8Si_8O_{12}$ from 4000 to 40 cm^{-1} . In the range from 4000 to 700 cm^{-1} in CCl_4 and below in a polyethylene wafer

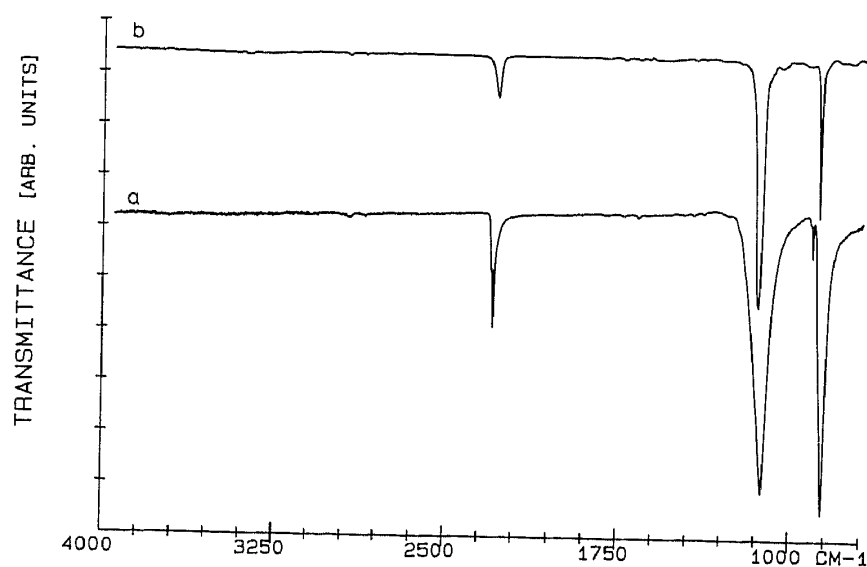


Fig. 3. Comparison of (a) the ATR-FTIR spectrum of $H_8Si_8O_{12}$ on ZnSe and of (b) the spectrum in CCl_4 from 4000 to 700 cm^{-1}

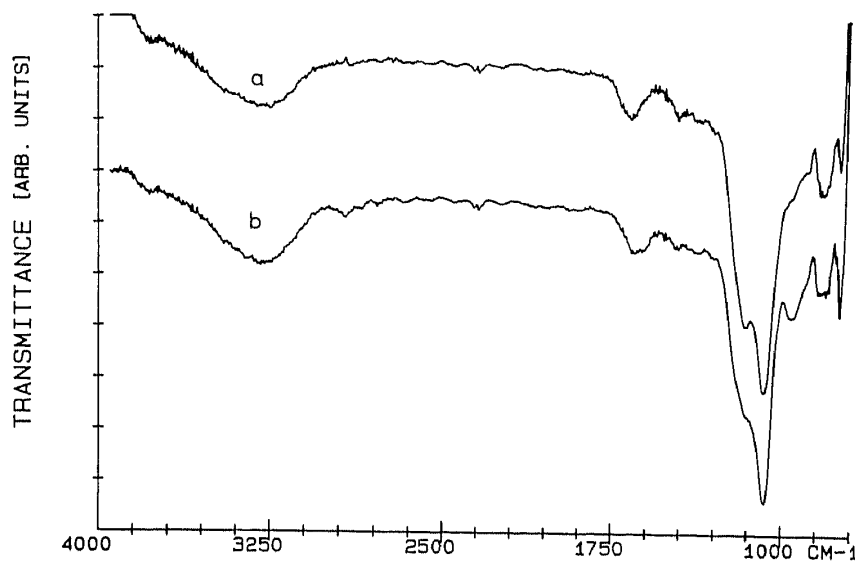


Fig. 4. ATR-FTIR spectrum of $\text{Cl}_8\text{Si}_8\text{O}_{12}$ on Ge; (a) after reacting with the surface OH groups; (b) after exposure to water

The qualitative features of both spectra are the same, however, the origin of the broadening and the small peak at 911 cm^{-1} observed on the crystal is not yet clear and needs further investigation.

In Fig. 4 we show the ATR spectrum of the $\text{Cl}_8\text{Si}_8\text{O}_{12}$ on Ge after reacting with the surface OH groups. The Ge crystal was first washed with EtOH and CCl_4 , dried under vacuum and plasma and cleaned for 20 min in an air plasma at 4 Pa. The reaction was carried out by immersing the SC crystal in a CCl_4 solution of $\text{Cl}_8\text{Si}_8\text{O}_{12}$ at 80°C for 12 h. After this time the crystal was rinsed with CCl_4 . Spectra were taken (a) immediately after this procedure and (b) after exposing the "reacted" crystal to water for 5 min. In (b) a new band at 951 cm^{-1} is formed. This implies that the band at 951 cm^{-1} is the SiO stretching mode of the free SiOH groups.

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